

FDN306P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

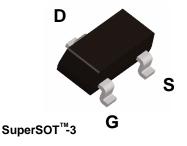
Applications

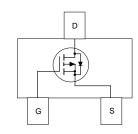
- · Battery management
- · Load switch
- Battery protection

Features

• -2.6 A, -12 V. $R_{DS(ON)} = 40 \ m\Omega$ @ $V_{GS} = -4.5 \ V$ $R_{DS(ON)} = 60 \ m\Omega$ @ $V_{GS} = -2.5 \ V$ $R_{DS(ON)} = 95 \ m\Omega$ @ $V_{GS} = -1.8 \ V$

- · Fast switching speed
- High performance trench technology for extremely low R_{DS(ON)}
- SuperSOT[™] -3 provides low R_{DS(ON)} and 30% higher power handling capability than SOT23 in the same footprint





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		-12	V
V_{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-2.6	А
	- Pulsed		-10	
P _D	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T_J , T_{STG}	Operating and Storage Junction Tem	perature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
306	FDN306P	7"	8mm	3000 units

Symbol	Parameter	Min	Тур	Max	Units		
Off Char	acteristics	•		I.		ı	I.
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V$,	$I_D = -250 \mu\text{A}$	-12			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A,R}$	eferenced to 25°C		-3		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V},$				-1	μΑ
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8 V$,				100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V},$	$V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$,	$I_D = -250 \mu\text{A}$	-0.4	-0.6	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu A, R$	eferenced to 25°C		2.5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},$ $V_{GS} = -2.5 \text{ V},$ $V_{GS} = -1.8 \text{ V},$ $V_{GS} = -4.5 \text{ V},$ I	$I_D = -2.3 \text{ A}$		30 39 54 40	40 50 72 54	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V},$		-10			Α
g _{FS}	Forward Transconductance	$V_{DS} = -5 V$,	$I_D = -2.6 \text{ A}$		10		S
Dynamic	: Characteristics						
C _{iss}	Input Capacitance	$V_{DS} = -6 \text{ V},$	V _{GS} = 0 V,		1138		pF
Coss	Output Capacitance	f = 1.0 MHz			454		pF
C _{rss}	Reverse Transfer Capacitance				302		pF
Switchin	g Characteristics (Note 2)						
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -6 \text{ V},$ $V_{GS} = -4.5 \text{ V},$	$I_D = -1 A$,		11	20	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V},$	$R_{GEN} = 6 \Omega$		10	20	ns
t _{d(off)}	Turn-Off Delay Time				38	61	ns
t _f	Turn-Off Fall Time				35	56	ns
Qg	Total Gate Charge	$V_{DS} = -6 V$,	$I_D = -2.6 \text{ A},$		12	17	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$			2		nC
Q_{gd}	Gate-Drain Charge				3		nC
Drain-S	ource Diode Characteristics	and Maximi	um Ratings				
Is	Maximum Continuous Drain-Source					-0.42	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$,	$I_S = -0.42$ (Note 2)		-0.6	-1.2	V

Notes

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

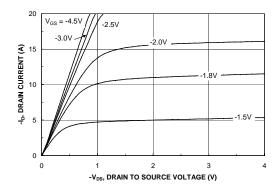


Figure 1. On-Region Characteristics.

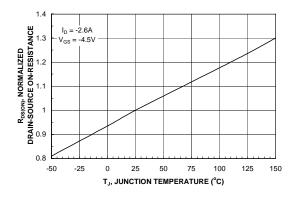


Figure 3. On-Resistance Variation with Temperature.

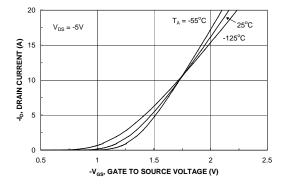


Figure 5. Transfer Characteristics.

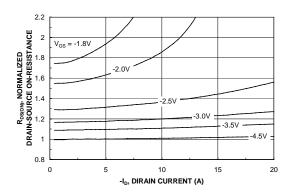


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

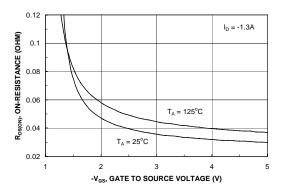


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

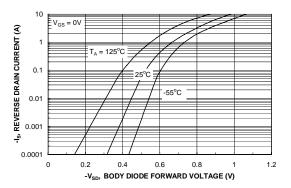
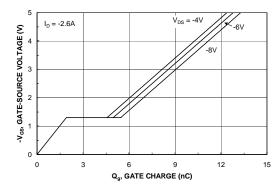


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



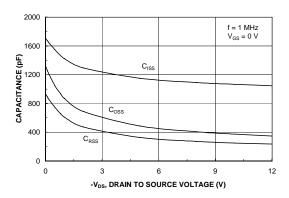
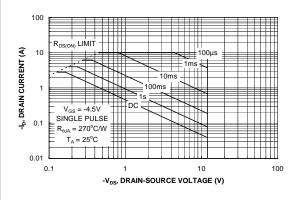


Figure 7. Gate Charge Characteristics.





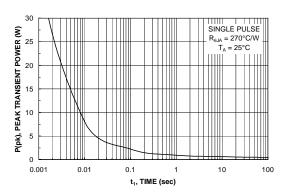


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

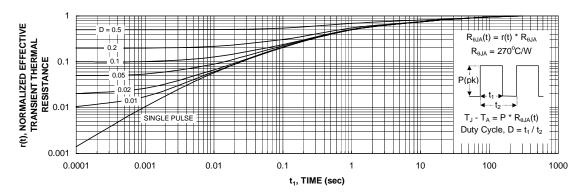
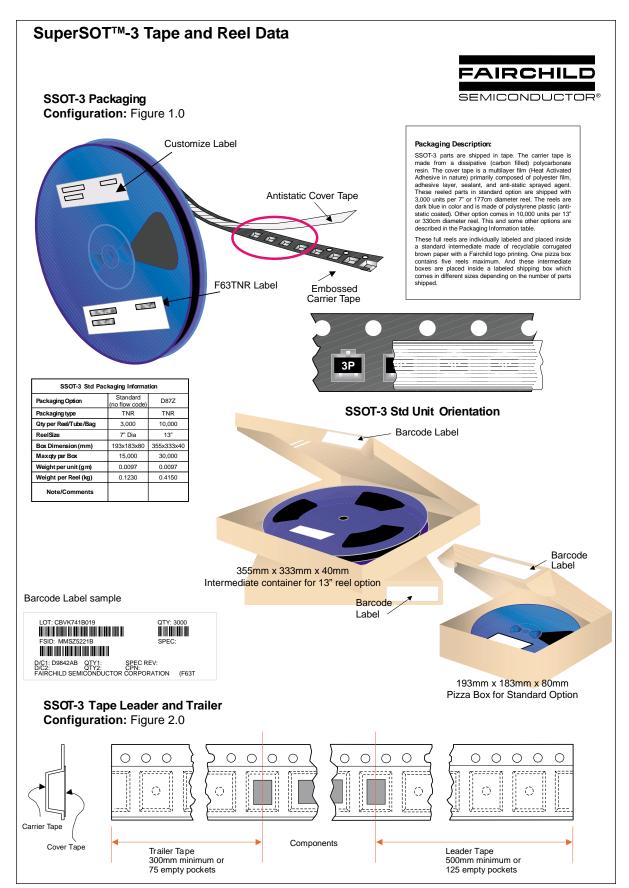


Figure 11. Transient Thermal Response Curve.

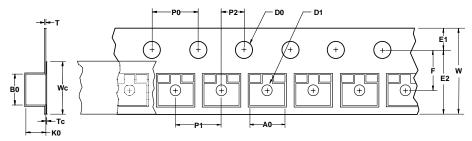
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

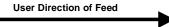




SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



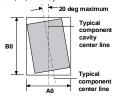


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

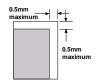
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

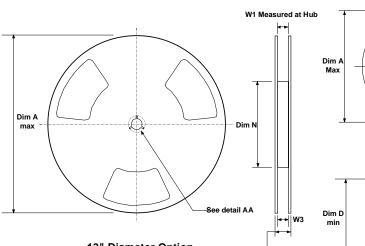


Sketch B (Top View)
Component Rotation

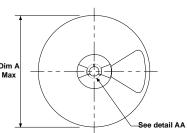


Sketch C (Top View)
Component lateral movement

SSOT-3 Reel Configuration: Figure 4.0





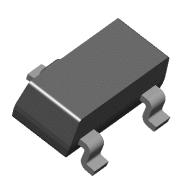


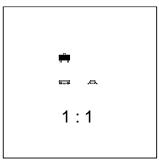
7" Diameter Option B Min Dim D min

	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	



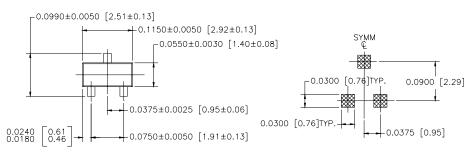
SuperSOT™-3 (FS PKG Code 32)



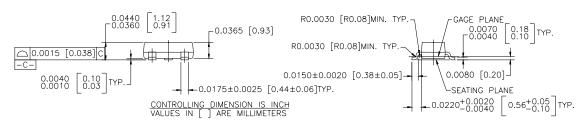


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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